

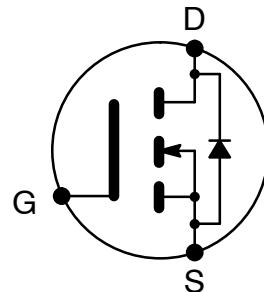


ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748-5089
<http://www.nteinc.com>

NTE2973
MOSFET
N-Channel, Enhancement Mode
High Speed Switch
TO3P Type Package

Applications:

- SMPS
- DC-DC Converter
- Battery Charger
- Power Supply of Printer
- Copier
- HDD, FDD, TV, VCR
- Personal Computer



Absolute Maximum Ratings: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

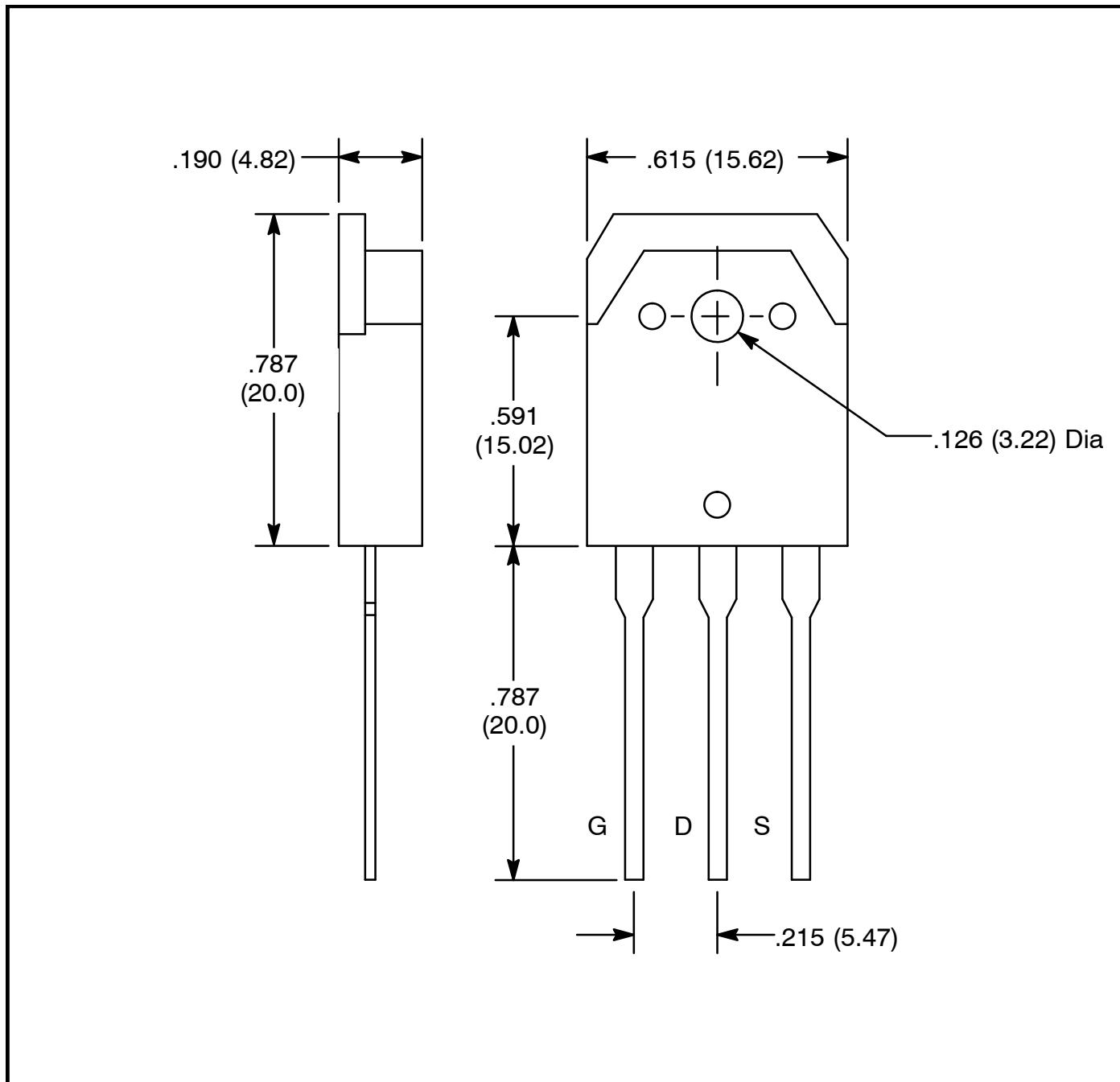
Drain-Source Voltage ($V_{GS} = 0\text{V}$), V_{DSS}	900V
Gate-Source Voltage ($V_{DS} = 0\text{V}$), V_{GS}	$\pm 30\text{V}$
Drain Current, I_D	
Continuous	14A
Pulsed	42A
Maximum Power Dissipation, P_D	275W
Channel Temperature Range, T_{ch}	-55° to +150°C
Storage Temperature Range, T_{stg}	-55° to +150°C
Thermal Resistance, Channel-to-Case, $R_{th(ch-c)}$	0.45°C/W

Electrical Characteristics: ($T_{ch} = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{DS} = 0\text{V}$, $I_D = 1\text{mA}$	900	-	-	V
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$V_{DS} = 0\text{V}$, $I_G = \pm 100\text{A}$	± 30	-	-	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 25\text{V}$, $V_{DS} = 0\text{V}$	-	-	± 10	mA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 900\text{V}$, $V_{GS} = 0$	-	-	1.0	mA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = 10\text{V}$, $I_D = 1\text{mA}$	2.0	3.0	4.0	V
Static Drain-Source ON Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 7\text{A}$	-	0.63	0.85	\pm
Drain-Source On-State Voltage	$V_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 7\text{A}$	-	4.41	5.95	V
Forward Transfer Admittance	$ y_{fs} $	$V_{GS} = 10\text{V}$, $I_D = 7\text{A}$	9	15	-	S

Electrical Characteristics (Cont'd): ($T_{ch} = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$	-	2900	-	pF
Output Capacitance	C_{oss}		-	290	-	pF
Reverse Transfer Capacitance	C_{rss}		-	50	-	pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 200\text{V}, I_D = 7\text{A}, V_{GS} = 10\text{V}, R_{GEN} = R_{GS} = 50\pm$	-	45	-	ns
Rise Time	t_r		-	65	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	325	-	ns
Fall Time	t_f		-	100	-	ns
Diode Forward Voltage	V_{SD}	$I_S = 7\text{A}, V_{GS} = 0\text{V}$	-	1.0	1.5	V



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [NTE manufacturer](#):

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [FW216A-TL-2W](#) [FW231A-TL-E](#) [APT5010JVR](#) [NTNS3A92PZT5G](#)
[IRF100S201](#) [JANTX2N5237](#) [2SK2464-TL-E](#) [2SK3818-DL-E](#) [FCA20N60_F109](#) [FDZ595PZ](#) [STD6600NT4G](#) [FSS804-TL-E](#) [2SJ277-DL-E](#)
[2SK1691-DL-E](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MCH6646-TL-E](#) [TPCC8103,L1Q\(CM](#) [367-8430-0972-503](#) [VN1206L](#) [424134F](#)
[026935X](#) [051075F](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [751625C](#) [873612G](#) [IRF7380TRHR](#) [IPS70R2K0CEAKMA1](#)
[RJK60S3DPP-E0#T2](#) [RJK60S5DPK-M0#T0](#) [APT5010JVFR](#) [APT12031JFLL](#) [APT12040JVR](#) [DMN3404LQ-7](#) [NTE6400](#) [JANTX2N6796U](#)
[JANTX2N6784U](#) [JANTXV2N5416U4](#) [SQM110N05-06L-GE3](#) [SIHF35N60E-GE3](#) [2SK2614\(TE16L1,Q\)](#)